

PURE STRIP

STABILIZED SULFURIC ACID-HYDROGEN PEROXIDE COMPOUND

DESCRIPTION:

Pure Strip is suitable for stripping both positive and negative photoresists in addition to other organic compounds in a variety of semiconductor, photomask, and IC photolithography compounds. High yields can be achieved due to the high purity/low particulate composition of Pure Strip.

Advantages Pure Strip include negligible attack on exposed metal surfaces, including aluminum, vs. other acidic formulations, residue-free rinsing, and extended bath life (minimum of five days at room temperature). Pure Strip is ready to use and requires no mixing.

TYPICAL ASSAY:

HYDROGEN PEROXIDE ASSAY	< 1%
PEROXYMONOSULFURIC ACID ASSAY	4.0-5.15%
SULFURIC ACID ASSAY	89-91%

APPLICATION:

Pure Strip may be used at room temperature or at elevated temperature. Higher temperatures will increase the activity but decrease the bath life (1 day at 60-80 °C). Substrates are stripped of photoresist and cleaned effectively with minimal attack on aluminum (approximately 35 angstroms/minute at room temperature) and negligible attack on other metals and alloys such as titanium, ti-tungsten, copper, tantalum silicide, and ITO.

TRANSENE
COMPANY, INC.